

Listing of Claims:

Claim 1 (previously presented) A wafer carrier for carrying a wafer, comprising:

a transparent base;

a conducting layer positioned on a bottom surface of the transparent base; and

5 a bonding layer positioned on a top surface of the wafer carrier for bonding the wafer and the transparent base together;

wherein the wafer carrier is attracted by an electrostatic chuck via the conducting layer.

10 Claim 2 (original) The wafer carrier of claim 1, wherein the transparent base has dimensions similar to that of the wafer.

Claim 3 (original) The wafer carrier of claim 1, wherein the transparent base is a glass wafer.

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Claim 4 (original) The wafer carrier of claim 1, wherein the transparent base is a quartz wafer.

Claim 5 (cancelled)

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Claim 6 (previously presented) The wafer carrier of claim 1, wherein the bonding layer is selected from the group consisting of double-sided tape, ultra violet tape, thermal sensitive tape, photo resist, and wax.

25 Claim 7 (previously presented) The wafer carrier of claim 1, wherein the wafer is transferred and undergoes at least a semiconductor process.

Claim 8 (original) The wafer carrier of claim 7, wherein the semiconductor process is a

double-sided process, and the wafer comprises at least an alignment mark.

Claim 9 (original) The wafer carrier of claim 8, wherein the conducting layer is a transparent conducting layer.

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Claim 10 (original) The wafer carrier of claim 8, wherein the conducting layer is a non-transparent conducting layer having at least an exposed region corresponding to the alignment mark.

10 Claim 11 (original) The wafer carrier of claim 10, wherein the non-transparent conducting layer comprises a plurality of conducting patterns connected with each other.

Claim 12 (previously presented) A wafer carrier adapted for use in a double-sided process for carrying a wafer, comprising:

15 a transparent base;
a conducting layer positioned on a bottom surface of the transparent base, wherein the wafer carrier is attracted by an electrostatic chuck via the conducting layer;
and
a bonding layer positioned on a top surface of the transparent base for bonding the
20 wafer and the transparent base.

Claim 13 (original) The wafer carrier of claim 12, wherein the transparent base has dimensions similar to that of the wafer.

25 Claim 14 (original) The wafer carrier of claim 12, wherein the transparent base is a glass wafer.

Claim 15 (original) The wafer carrier of claim 12, wherein the transparent base is a quartz

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wafer.

Claim 16 (original) The wafer carrier of claim 12, wherein the bonding layer is selected from the group consisting of double-sided tape, ultra violet tape, thermal sensitive tape,
5 photo resist, and wax.

Claim 17 (previously presented) The wafer carrier of claim 12, wherein—the wafer is transferred and undergoes the double-sided process.

10 Claim 18 (original) The wafer carrier of claim 17, wherein the wafer comprises at least an alignment mark.

Claim 19 (original) The wafer carrier of claim 18, wherein the conducting layer is a transparent conducting layer.

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Claim 20 (original) The wafer carrier of claim 18, wherein the conducting layer is a non-transparent conducting layer having at least an exposed region corresponding to the alignment mark.

20 Claim 21 (original) The wafer carrier of claim 12, wherein the non-transparent conducting layer comprises a plurality of conducting patterns connected with each other.